NSN 5961-01-100-5885

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View Online at https://aerobasegroup.com/nsn/5961-01-100-5885 **Inclosure Material:** Metal **Overall Length:** Between 0.250 inches and 0.450 inches **Terminal Length:** Between 0.440 inches and 0.480 inches **Overall Diameter:** 0.875 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-3 **Electrode Internally-electrically Connected To Case:** Collector **Mounting Method:** Terminal and unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 120.0 breakdown voltage, collector-to-base, emitter open and 120.0 breakdown voltage, collector-to-emitter, base open and 7.0 breakdown voltage, emitter-to-base, collector open **Current Rating Per Characteristic:** Between 5.00 amperes source cutoff current and 10.00 amperes source cutoff current **Power Rating Per Characteristic:** 150.0 watts small-signal input power, common-collector absolute **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Junction pattern arrangement: pnp **Terminal Type And Quantity:** 1 case and 2 pin **Specification Data:** 80131-release6334 professional/industrial association specification Shelf Life: N/a **Unit Of Measure:**

Demilitarization: Yes - demil/mli

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